

SSM7811GM-VB Datasheet

N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
20	0.0049 at $V_{GS} = 4.5$ V	20 ^e	27.5 nC
	0.0056 at $V_{GS} = 2.5$ V	20 ^e	

FEATURES

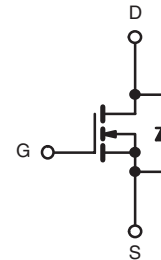
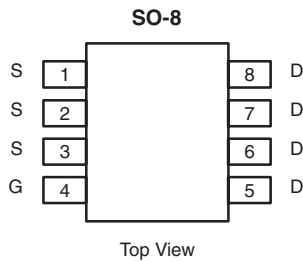
- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Low-Side MOSFET for Synchronous Buck
 - Game Machine
 - PC



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 16	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	20 ^e	A
	$T_C = 70$ °C	18.2	
	$T_A = 25$ °C	15.2 ^{b, c}	
	$T_A = 70$ °C	12.1 ^{b, c}	
Pulsed Drain Current	I_{DM}	50	A
Continuous Source-Drain Diode Current	$T_C = 25$ °C	5.1	
	$T_A = 25$ °C	2.2 ^{b, c}	
Single Pulse Avalanche Current	I_{AS}	30	
Avalanche Energy	E_{AS}	45	mJ
Maximum Power Dissipation	$T_C = 25$ °C	5.7	W
	$T_C = 70$ °C	3.6	
	$T_A = 25$ °C	2.5 ^{b, c}	
	$T_A = 70$ °C	1.6 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	39	50	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	18	22	

Notes:

- Based on $T_C = 25$ °C.
- Surface Mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- Maximum under Steady State conditions is 85 °C/W.
- Package limited.

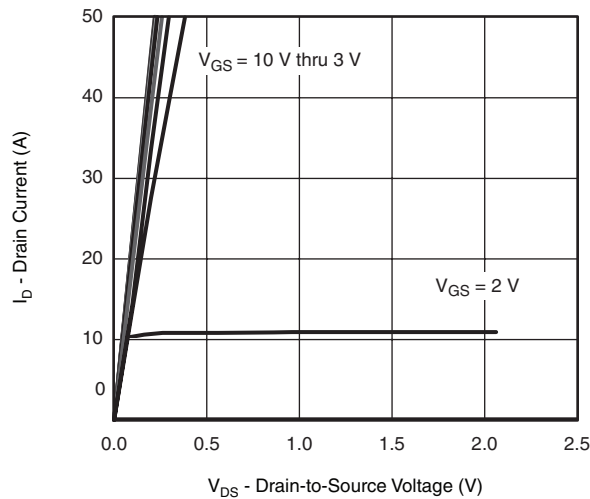
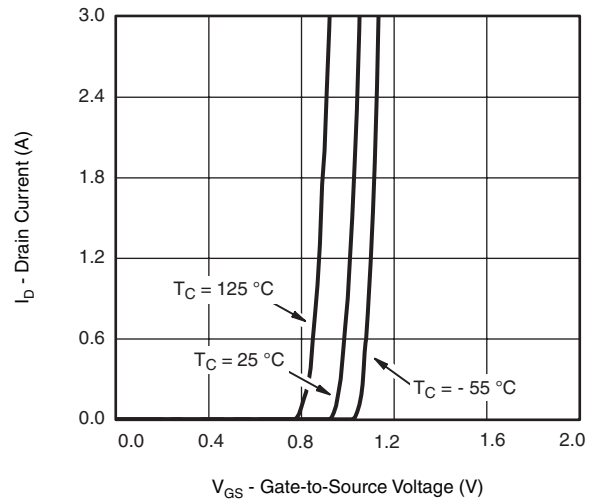
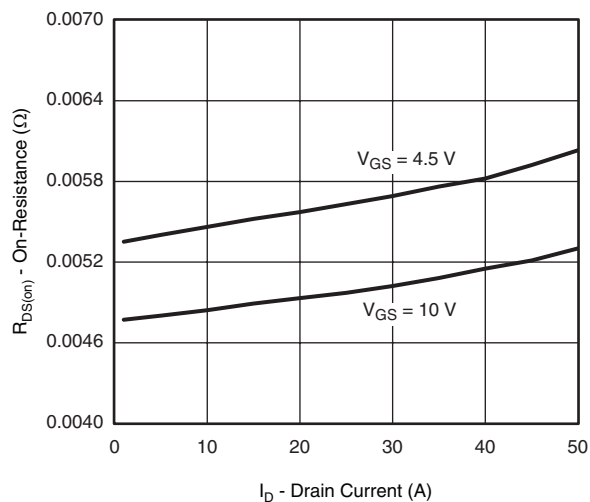
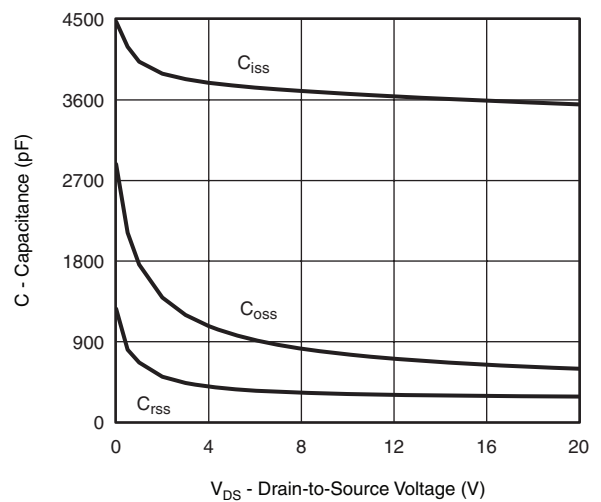
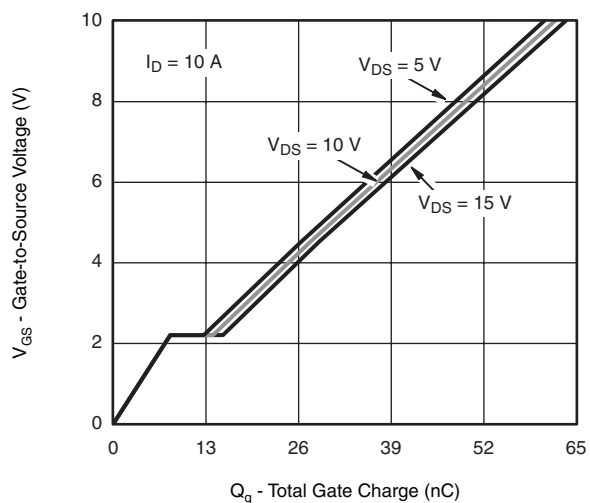
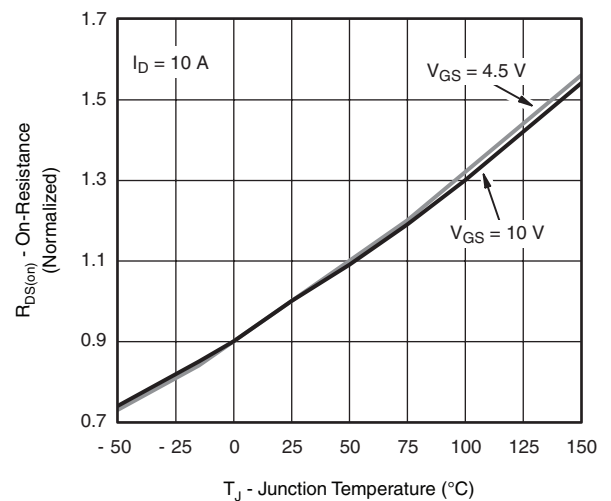
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	20			V	
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		19		mV/°C	
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 5.3			
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0		2.1	V	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 16 V			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1	μA	
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C			10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	30			A	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 10 A		0.0049		Ω	
		V _{GS} = 2.5 V, I _D = 7 A		0.0056			
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 10 A		55		S	
Dynamic ^b							
Input Capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		3700		pF	
Output Capacitance	C _{oss}			745			
Reverse Transfer Capacitance	C _{rss}			315			
Total Gate Charge	Q _g	V _{DS} = 10 V, V _{GS} = 10 V, I _D = 10 A		62	95	nC	
Gate-Source Charge	Q _{gs}	V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 10 A		27.5	42		
Gate-Drain Charge	Q _{gd}			8.0			
Gate Resistance	R _g			6.0			
Turn-On Delay Time	t _{d(on)}	f = 1 MHz	0.15	0.7	1.4	Ω	
Rise Time	t _r		V _{DD} = 10 V, R _L = 2 Ω I _D ≅ 5 A, V _{GEN} = 4.5 V, R _g = 1 Ω		30	55	ns
Turn-Off Delay Time	t _{d(off)}				13	25	
Fall Time	t _f				60	100	
Turn-On Delay Time	t _{d(on)}			30	55		
Rise Time	t _r	V _{DD} = 10 V, R _L = 2 Ω I _D ≅ 5 A, V _{GEN} = 10 V, R _g = 1 Ω		13	25		
Turn-Off Delay Time	t _{d(off)}			9	18		
Fall Time	t _f			38	65		
				8	16		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			5.1	A	
Pulse Diode Forward Current ^a	I _{SM}				50		
Body Diode Voltage	V _{SD}	I _S = 2 A		0.71	1.1	V	
Body Diode Reverse Recovery Time	t _{rr}	I _F = 10 A, dI/dt = 100 A/μs, T _J = 25 °C		26	50	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			16	30	nC	
Reverse Recovery Fall Time	t _a			13		ns	
Reverse Recovery Rise Time	t _b			13			

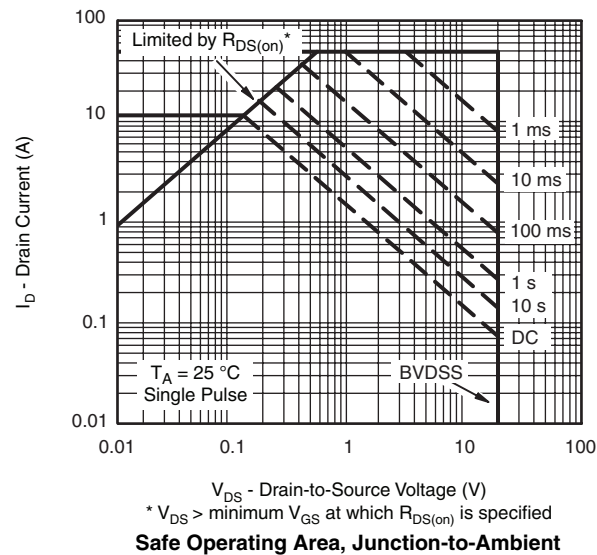
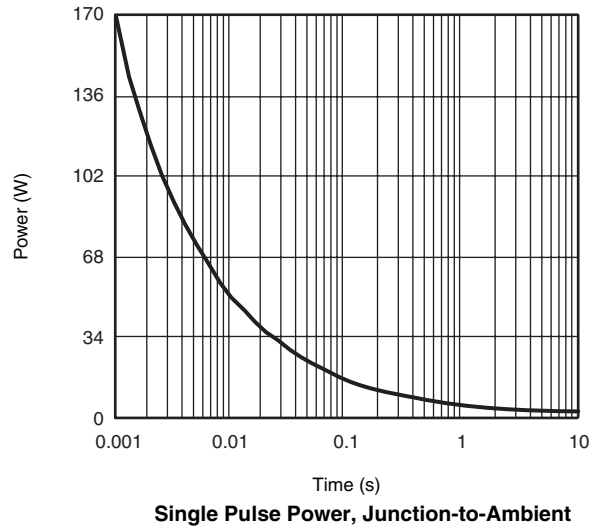
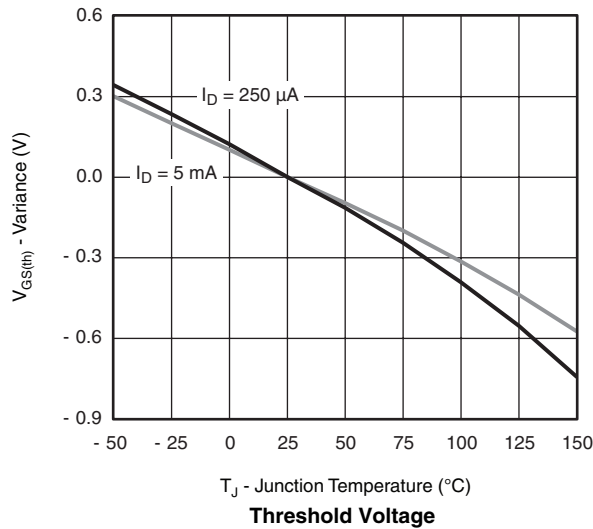
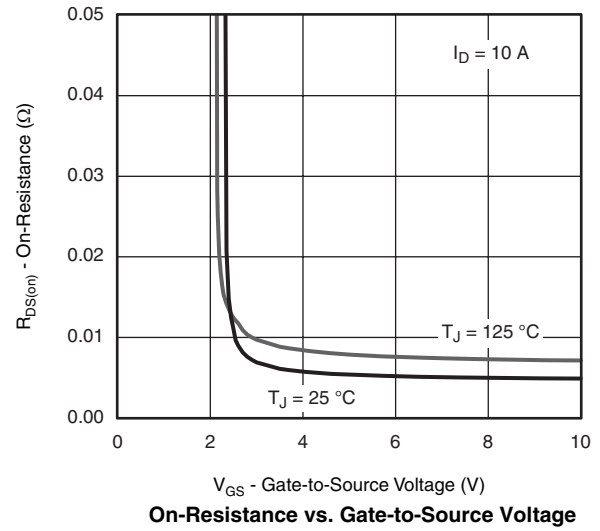
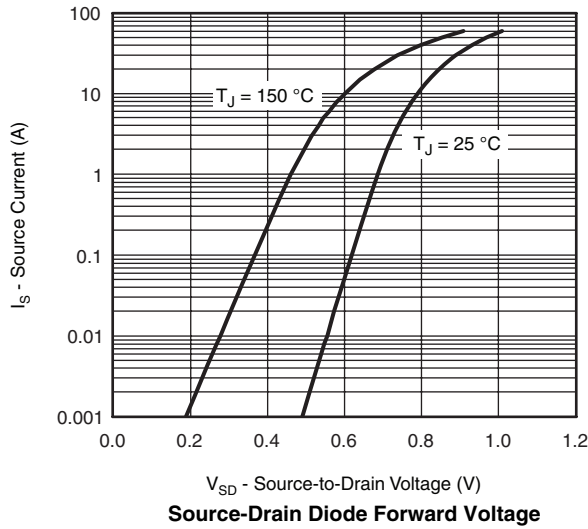
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

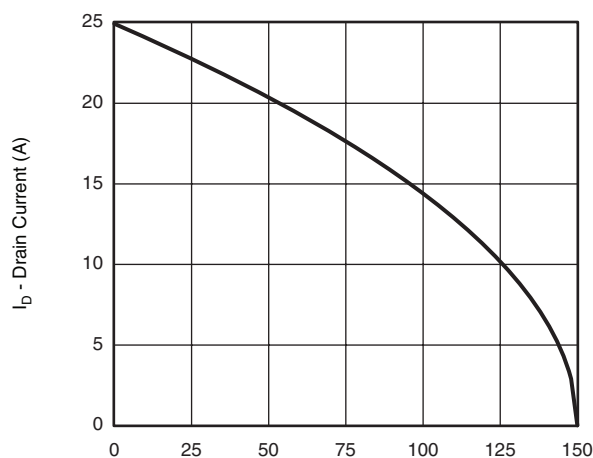
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

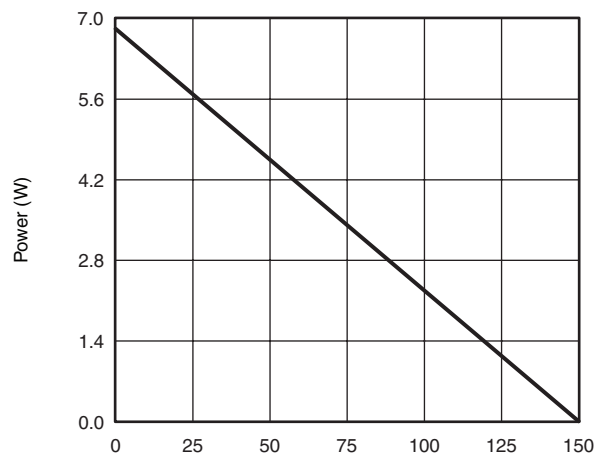
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current and Gate Voltage

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

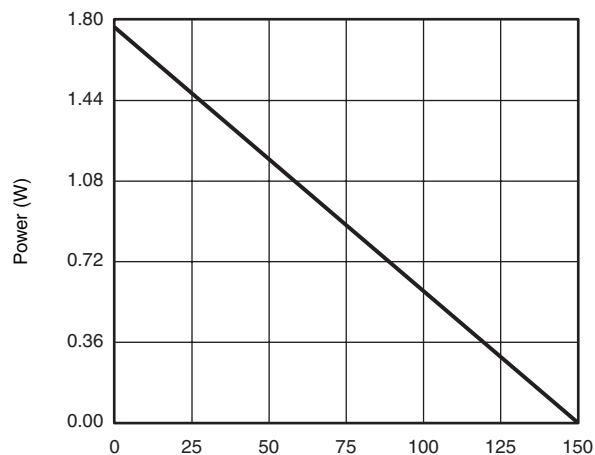
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

 V_{DS} - Drain-to-Source Voltage (V)

 * $V_{DS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

 T_C - Case Temperature (°C)

Current Derating*

 T_C - Case Temperature (°C)

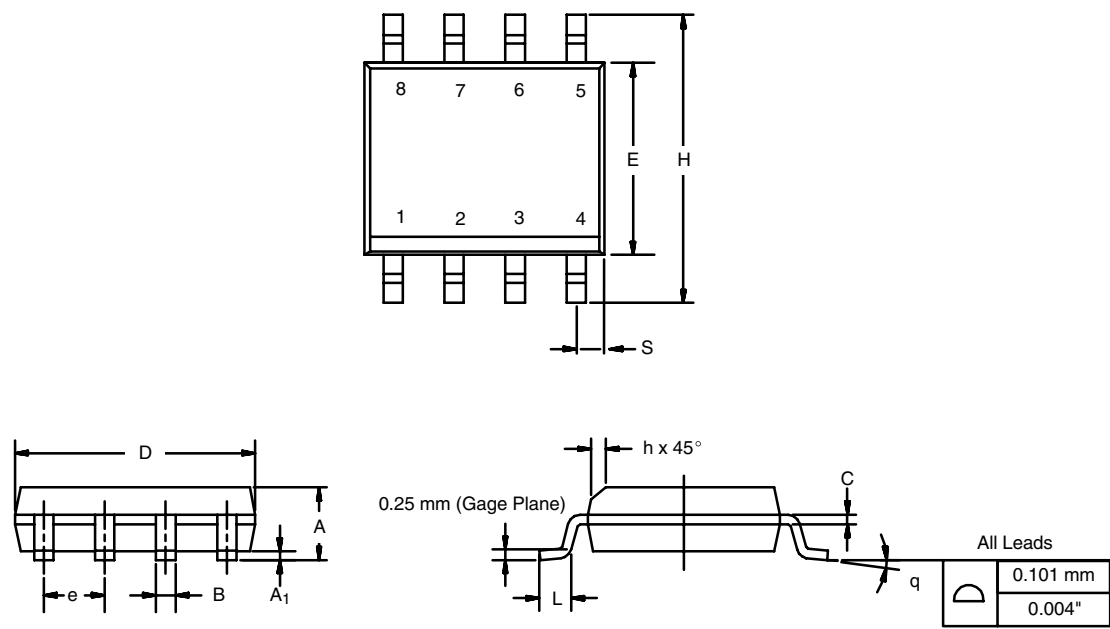
Power, Junction-to-Foot

 T_A - Ambient Temperature (°C)

Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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